Improve business performance in just nanoseconds.

Advanced 2.5" SSD designed for read-intensive, data-streaming data centers. Gain a timely advantage with Samsung 860 DCT Series SSD. Designed specifically to meet and exceed the unique requirements of read-intensive, data-streaming data centers, it'll quickly improve your business' performance, value and reliability. The 860 DCT Series SSD also features Samsung's groundbreaking V-NAND technology, best-in-class TBW levels and a reinforced controller. It's advanced technology designed to make a difference right away.

Make a difference, faster than ever.

Data Center SSDs, Advanced V-NAND

Keep your business running 24/7. Attain optimal performance, value and reliability with advanced Samsung V-NAND technology SSDs. They're produced in-house to stringent standards and are designed specifically to enhance your read-intensive, data-streaming data center.

Optimal Read-Intensive Performance

Give speed to your business presence. Boost performance with faster sequential and random read speeds. They're ideal for all types of read-intensive, data-streaming data centers, including content delivery network systems.

Enhanced Operations Efficiency

Accomplish far more with less. Achieve higher efficiency and performance compared to legacy storage systems, with fewer servers, reduced power and cooling, and lower TCO. Maintenance is more efficient, too, with the provided Samsung SSD Toolkit software.

Samsung Quality and Reliability

Keep going with less downtime. In-house production utilizing our own Samsung-built components allows us greater quality control and manufacturing efficiencies, to produce SSDs of superior quality and reliability. Empower your business to run faster, more efficiently, and with the reduced costs that come from world-class dependability.

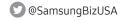|		MZ-76E960E / MZ-76E1T9E / MZ-76E3T8E
Usage Application		Data Center
Capacity[1]		960 GB / 1920 GB (1.9 TB) / 3840 GB (3.8 TB)
Interface		SATA 6 Gb/s (Compatible with SATA 3 Gb/s and SATA 1.5 Gb/s)
Controller		Samsung MJX Controller
NAND Flash Memory		Samsung V-NAND 3-bit MLC
DRAM Cache Memory		1 GB LPDDR4 SDRAM / 2 GB LPDDR4 SDRAM / 4 GB LPDDR4 SDRAM
Performance[2]	4KB Sequential Read (Max.)	550 MB/s
	4KB Sequential Write (Max.)	520 MB/s
	4KB Random Read (QD32) (Max.)	98,000 IOPS
	4KB Random Write (QD32) (Max.)	19,000 IOPS
Reliability (MTBF)		1.5 Million Hours
TBW (Terabytes Written)[3]		349 TBW / 698 TBW / 1,396 TBW
Supporting Features		TRIM Support, Garbage Collection, S.M.A.R.T., AES 256-bit Encryption (Class 0), WWN Support
Vibration (Non-Operating)		20~2000Hz, 20G
Shock (Non-Operating)[4]		1500G, Duration 0.5 m/sec, Half-Sine
Limited Warranty[5]		3 Years or 349 TBW / 3 Years or 698 TBW / 3 Years or 1,396 TBW

Learn More   samsung.com/business   insights.samsung.com   samsung.com/b2bssd

Product Support   1-866-SAM4BIZ

Follow Us   youtube.com/samsungbizusa   @SamsungBizUSA

SAMSUNG

[1] 1 GB=1,000,000,000 bytes, unformatted capacity. User accessible capacity may vary depending on operating environment and formatting. [2] Performance measured using FIO 2.18 with queue depth 32, Z170 Intel SATA 6G port. Measurements are performed on entire LBA range. Write cache enabled. Performance may vary depending on capacity. [3] All documented endurance test results are obtained in compliance with JESD218 standards. Please visit jedec.org for detailed information on JESD218 standards. [4] Internal free fall shock test conducted under controlled conditions. [5] Warranty 5 years or TBW, whichever comes first. For more information on the warranty, please find the warranty statement enclosed in the package.